

METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

BACKGROUND OF THE INVENTION

The present invention relates to a method for fabricating a semiconductor device having a capacitor.

5 A semiconductor device having a capacitor which uses a ferroelectric film or a high dielectric film as a capacitor insulating film has a remanent polarization resulting from a hysteresis characteristic or a high specific dielectric constant. In the field of a nonvolatile memory and a DRAM, therefore, a possibility is that a capacitor using a ferroelectric film or a high dielectric film as a capacitor insulating film will be used widely
10 as a replacement for a capacitor having a capacitor insulating film composed of a silicon oxide film or a silicon nitride film. In this case, a capacitor is requested to have a three-dimensional configuration for a further reduction in the area of a memory cell.

A conventional method for fabricating a semiconductor device will be described herein below with reference to FIGS. 16A to 16C and FIGS. 17A to 17C.

15 First, as shown in FIG. 16A, a first silicon oxide film 11 is formed by CVD on a semiconductor substrate 10 and then planarized by CMP. Then, selective dry etching is performed with respect to the first silicon oxide film 11 to form a contact hole for exposing the semiconductor substrate 10. Subsequently, a titanium film and a titanium nitride film are formed by sputtering or CVD in such a manner as to fill in the contact hole and a
20 tungsten film is further formed by CVD.

Next, a metal film composed of the titanium film, the titanium nitride film, and the tungsten film is left only in the contact hole by CMP to form a plug 12. Then, a multilayer film composed of a titanium-aluminum nitride film, an iridium film, and an iridium oxide film which are stacked successively in layers are formed by sputtering over
25 the first silicon oxide film 11 and the plug 12. Subsequently, selective dry etching is

performed with respect to the multilayer film, thereby forming an oxygen barrier film 13 covering the plug 12.

Next, as shown in FIG. 16B, a second silicon oxide film 14 is formed over the first silicon oxide film 11 in such a manner as to cover the oxygen barrier film 13 and then planarized by CMP. Then, as shown in FIG. 16C, a resist mask 15 having an opening pattern 15a above the oxygen barrier layer 13 is formed on the second silicon oxide film 14.

Next, as shown in FIG. 17A, etching is performed with respect to the second silicon oxide film 14 by using the resist mask 15 having the opening pattern 15a, thereby forming an opening 14a for exposing the oxygen barrier film 13. In this case, the oxygen barrier film 13 is over etched and the film thickness of the resist mask 15 is reduced by etching.

Next, as shown in FIG. 17B, the remaining resist mask 15 is removed by ashing. Then, as shown in FIG. 17C, a first platinum film is formed by sputtering over the second silicon oxide film 14 and in the opening 14a. Subsequently, selective dry etching is performed with respect to the first platinum film in a region including the opening 14a, thereby forming a lower electrode 16 composed of the patterned first platinum film. Then, a ferroelectric film composed of a bismuth layer-structured Perovskite-type oxide, the components of which are strontium, bismuth, tantalum, and niobium, is formed by MOCVD over the second silicon oxide film 14 and the lower electrode 16. After a second platinum film is then formed by sputtering on the ferroelectric film, the ferroelectric film and the second platinum film are patterned in a region including the lower electrode 16, whereby a capacitor insulating film 17 and an upper electrode 18 are formed. Thereafter, wiring, a protective film, and the like are formed, though they are not disclosed.

In accordance with the foregoing fabrication method, however, the coverage of the lower electrode 16, the capacitor insulating film 17, and the upper electrode 18

composing a capacitor is insufficient so that the cross section of the capacitor is likely to have an overhung configuration. Consequently, a broken wire may occur in the lower electrode 16 or in the upper electrode 18. In addition, the film thickness of the capacitor becomes smaller with approach toward the bottom portion of the wall surface of the opening 14a, while the film thickness of the capacitor is also reduced at the bottom portion of the opening 14a. Since the coverage is insufficient, variations occur in the characteristics of the capacitor if the thickness of the capacitor insulating film 17 becomes nonuniform.

There are cases where the lower electrode, the capacitor insulating film, and the upper electrode, which are formed when the opening has a vertical configuration in accordance with another conventional method for fabricating a semiconductor device, are not shown in such an inferior coverage condition as shown in FIG. 17C. If sputtering which allows simple and convenient film formation for the upper electrode, the lower electrode, or the capacitor insulating film is used, however, coverage deteriorates in the opening in an actual situation (see, e.g., U.S. Pat. No. 6,239,461, column 5 line 44 to column 6 line 26, FIG. 5). Even if MOCVD (Metal Organic CVD) which relatively improves the coverage is used, coverage is insufficient in practice and the new problem of a lower film-forming rate is encountered if the coverage is to be improved by using the method.

To improve the coverage of the electrodes and the capacitor insulating film, a method of forming the wall surface of the opening into a downwardly tapered configuration when viewed from above (it is assumed hereinafter that, if any mention is made of the configuration of the wall surface in the following description, it refers to a configuration viewed from above). To form an extremely small opening in a silicon oxide film used typically as an interlayer insulating film, it is necessary to form the opening by

dry etching. However, reactive etching cannot be performed with respect to a silicon oxide film so that it is difficult to form the wall surface of the opening into a downwardly tapered configuration.

As a method for forming the wall surface of an opening into a downwardly tapered configuration, there has been proposed a method which retracts a resist mask after forming an opening and performs etching again to form the wall surface of the opening into a downwardly tapered configuration (see, e.g., Japanese Laid-Open Patent Publication No. SHO 61-296722, pp. 2 to 3, FIG. 1). In this case, however, an underlying conductive film removed by etching for forming the opening is adhered again to the sidewall of the resist mask used for etching or a reaction product between an etching gas and the conductive film is deposited. The re-adhered conductive film and the reaction product remaining unremoved even after the retraction of the resist mask causes configurational abnormality such as the formation of a fence. In the case of performing etching again, therefore, the configurational abnormality hinders stable formation of the tapered configuration of the wall surface of the opening.

Thus, in accordance with the conventional method for fabricating a semiconductor device, the coverage of the electrodes and the capacitor insulating film is insufficient and the cross sections thereof are likely to present overhung configurations. If the coverage of the electrodes deteriorates, a broken wire occurs in the electrode. If the electrodes present overhung configurations, the width of the space in the upper portion of the opening is reduced so that the coverage of the capacitor insulating film is further degraded. This leads to a leakage current flowing in the capacitor insulating film and variations in the characteristics of the capacitor.

In the case of forming the capacitor insulating film by MOCVD (Metal Organic CVD), on the other hand, the raw materials of organic metals are supplied at nonuniform

rates so that the composition of the capacitor insulating film becomes nonuniform. In addition, a method for stably forming the tapered configuration of the wall surface of the opening is unknown.

SUMMARY OF THE INVENTION

5 In view of the foregoing, it is therefore an object of the present invention to stably form the wall surface of an opening into a tapered configuration and thereby improve the coverage of electrodes and a capacitor insulating film.

To attain the object, a first method for fabricating a semiconductor device according to the present invention comprises the steps of: forming a conductive film on a
10 substrate; forming an insulating film such that the conductive film is covered with the insulating film; forming, in the insulating film, a hole having a bottom portion not reaching the conductive film by using a mask having a first opening pattern; and forming, in the insulating film, an opening for exposing the conductive film by using a mask having a
15 second opening pattern having an opening diameter larger than an opening diameter of the first opening pattern, an obtuse angle being formed between a wall surface of the opening and a bottom surface of the opening.

Since the first method for fabricating a semiconductor device forms the hole not reaching the conductive film by the first etching using the mask having the first opening pattern and then exposes the conductive film by the second etching using the mask having
20 the second opening pattern having the opening diameter larger than that of the first opening pattern to form the opening, there is no such a situation that the conductive film is adhered again to the sidewall of the mask having the first opening pattern and a reaction product between an etching gas and the conductive film is deposited on the sidewall of the mask having the first opening pattern so that configurational abnormality, such as the formation
25 of a fence, which has been observed in a conventional embodiment does not occur.

Accordingly, the configuration of the wall surface of the opening can be formed smoothly and stably.

Preferably, the first method for fabricating a semiconductor device further comprises the step of: forming, at least in the opening, a capacitor element composed of a lower electrode, a capacitor insulating film, and an upper electrode.

The arrangement allows the formation of the electrodes and the capacitor insulating film which are excellent in coverage and prevents a broken wire in the electrode as well as a leakage current and a compositional deviation in the capacitor insulating film, thereby preventing variations in the characteristics of the capacitor element.

In the first method for fabricating a semiconductor device, the step of forming the capacitor element preferably includes the steps of: forming the lower electrode such that the wall surface of the opening and the bottom surface of the opening are covered with the lower electrode; forming the capacitor insulating film on the lower electrode; and forming the upper electrode on the capacitor insulating film.

In the first method for fabricating a semiconductor device, each of the lower electrode and the upper electrode may appropriately contain a platinum group element as a main component.

In the first method for fabricating a semiconductor device, the capacitor insulating film is preferably composed of a ferroelectric film or a high dielectric film.

In the first method for fabricating a semiconductor device, the capacitor insulating film is preferably composed of $\text{SrBi}_2(\text{Ta}_x\text{Nb}_{1-x})_2\text{O}_9$, $\text{Pb}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$, $(\text{Ba}_x\text{Sr}_{1-x})\text{TiO}_3$, $(\text{Bi}_x\text{La}_{1-x})_4\text{Ti}_3\text{O}_{12}$ (where X satisfies a relationship represented by $0 \leq x \leq 1$), or Ta_2O_5 .

In the first method for fabricating a semiconductor device, if the conductive film is composed of iridium, platinum, gold, ruthenium, rhodium, palladium, or a metal oxide thereof or alternatively composed of titanium, titanium-aluminum, tantalum, tantalum-

aluminum, a nitride thereof, or a multilayer film composed thereof, the re-adhesion of the conductive film removed by the etching to the mask can be suppressed and the deposition of the reaction product between the etching gas and the conductive film on the mask can be suppressed.

5 In the first method for fabricating a semiconductor device, if the conductive film contains an oxygen barrier film connected to the substrate via a plug, there is no such a situation that the plug is oxidized during the formation of the capacitor insulating film. This allows a connection between the capacitor element and the substrate.

10 In the first method for fabricating a semiconductor device, if the insulating film is an oxide film containing silicon, highly anisotropic etching can be performed with respect to the insulating film. By forming the opening by the second etching after forming the depressed portion by the first etching, therefore, a level difference at the wall surface of the opening is reduced and a smoothly tapered configuration is obtained.

15 In the first method for fabricating a semiconductor device, if the insulating film has a planarized principal surface, a focus shift in the mask used in forming the electrodes and the capacitor insulating film is reduced.

 In the first method for fabricating a semiconductor device, if the mask is a photoresist, the etching selectivity of the photoresist to the insulating film can be maintained sufficiently high.

20 A second method for fabricating a semiconductor device according to the present invention comprises the steps of: forming a conductive film on a specified region of a substrate; forming an insulating film on the substrate such that the conductive film is covered with the insulating film; forming, on the insulating film, a mask having a first opening pattern above the conductive film; performing first etching with respect to the
25 insulating film by using the mask having the first opening pattern to form, in the insulating

film, a depressed portion having a bottom portion not reaching the conductive film; forming a mask having a second opening pattern having an opening diameter larger than an opening diameter of the first opening pattern by enlarging the opening diameter of the first opening pattern; and performing second etching with respect to the insulating film by using
5 the mask having the second opening pattern to form, in the insulating film, an opening for exposing the conductive film such that the opening has a diameter larger than a diameter of the depressed portion and a wall surface having a tapered configuration.

Since the second method for fabricating a semiconductor device forms the depressed portion not reaching the conductive film by the first etching using the mask
10 having the first opening pattern and then exposes the conductive film by the second etching using the mask having the second opening pattern having the opening diameter larger than that of the first opening pattern to form the opening, there is no such a situation that the conductive film is adhered again to the sidewall of the mask having the first opening pattern and a reaction product between an etching gas and the conductive film is deposited
15 on the sidewall of the mask having the first opening pattern so that configurational abnormality, such as the formation of a fence, which has been observed in a conventional embodiment does not occur. Accordingly, the tapered configuration of the sidewall of the opening can be formed stably.

Preferably, the second method for fabricating a semiconductor device further
20 comprises the step of: forming, at least in the opening, a capacitor element composed of a lower electrode, a capacitor insulating film, and an upper electrode.

The arrangement allows the formation of the electrodes and the capacitor insulating film which are excellent in coverage and prevents a broken wire in the electrode as well as a leakage current and a compositional deviation in the capacitor insulating film,
25 thereby preventing variations in the characteristics of the capacitor element.

In the second method for fabricating a semiconductor device, the step of forming the capacitor element preferably includes the steps of: forming the lower electrode such that the wall surface of the opening and the bottom surface of the opening are covered with the lower electrode; forming the capacitor insulating film on the lower electrode; and
5 forming the upper electrode on the capacitor insulating film.

Preferably, the second method for fabricating a semiconductor device further comprises, between the step of forming the mask having the first opening pattern and the step of forming the depressed portion in the insulating film, the step of: forming a wall surface of the first opening pattern into a tapered configuration.

10 Since the arrangement performs the first etching after forming the wall surface of the first opening pattern into a tapered configuration, the wall surface of the opening can be processed into a more tapered configuration.

Preferably, the second method for fabricating a semiconductor device further comprises, after the step of forming the opening in the insulating film, the step of: after
15 removing the mask, performing third etching with respect to an entire surface of the insulating film to smooth the tapered configuration of the wall surface of the opening.

The arrangement allows the wall surface of the opening to have a smoothly tapered configuration.

Preferably, the second method for fabricating a semiconductor device further
20 comprises, after the step of forming the opening in the insulating film, the steps of: forming a mask having a third opening pattern having an opening diameter larger than the opening diameter of the second opening pattern by enlarging the opening diameter of the second opening pattern; and performing third etching with respect to the insulating film by using the mask having the third opening pattern to smooth the tapered configuration of the
25 wall surface of the opening.

The arrangement allows the wall surface of the opening to have a smoothly tapered configuration.

Preferably, the foregoing method for fabricating a semiconductor device further comprises, after the step of smoothing the tapered configuration of the wall surface of the opening, the step of: forming, at least in the opening, a capacitor element composed of a lower electrode, a capacitor insulating film, and an upper electrode.

The arrangement allows the formation of the electrodes and the capacitor insulating film which are excellent in coverage and prevents a broken wire in the electrode as well as a leakage current and a compositional deviation in the capacitor insulating film, thereby preventing variations in the characteristics of the capacitor element.

In the foregoing method for fabricating a semiconductor device, the step of forming the capacitor element preferably includes the steps of: forming the lower electrode such that the wall surface of the opening and the bottom surface of the opening are covered with the lower electrode; forming the capacitor insulating film on the lower electrode; and forming the upper electrode on the capacitor insulating film.

A third method for fabricating a semiconductor device according to the present invention comprises the steps of: forming a conductive film on a specified region of a substrate; forming an etching stopper film on the conductive film; forming an insulating film on the substrate such that the etching stopper film is covered with the insulating film; forming, on the insulating film, a mask having a first opening pattern above the conductive film; performing first etching with respect to the insulating film by using the mask having the first opening pattern to form, in the insulating film, a depressed portion having a bottom portion not reaching the etching stopper film; forming a mask having a second opening pattern having an opening diameter larger than an opening diameter of the first opening pattern by enlarging the opening diameter of the first opening pattern; performing

second etching with respect to the insulating film by using the mask having the second opening pattern to form, in the insulating film, an opening for exposing the etching stopper film such that the opening has a diameter larger than a diameter of the depressed portion and a wall surface having a tapered configuration; and performing third etching with respect to the etching stopper film to transfer the opening of the insulating film to the etching stopper film and thereby form, in the etching stopper film, an opening for exposing the conductive film, while smoothing the tapered configuration of the wall surface of the opening of the insulating film.

Since the third method for fabricating a semiconductor device forms the depressed portion not reaching the etching stopper film by the first etching using the mask having the first opening pattern and then forms the opening by the second etching using the mask having the second opening pattern having the opening diameter larger than that of the first opening pattern, there is no such a situation that the conductive film is adhered again to the sidewall of the mask having the first opening pattern and a reaction product between an etching gas and the conductive film is deposited on the sidewall of the mask having the first opening pattern so that configurational abnormality, such as the formation of a fence, which has been observed in a conventional embodiment does not occur. Accordingly, the tapered configuration of the sidewall of the opening can be formed stably. In contrast to the second method for fabricating a semiconductor device, the third method for fabricating a semiconductor device prevents the conductive film from being exposed in the opening formed by the second etching by forming the etching stopper film on the conductive film. This allows the wall surface of the opening to have a more smoothly tapered configuration through the third etching and suppresses an amount of over etching performed with respect to the conductive film during the third etching.

Preferably, the third method for fabricating a semiconductor device further

comprises the step of: forming a capacitor element composed of a lower electrode, a capacitor insulating film, and an upper electrode at least in the opening of the insulating film and in the opening of the etching stopper film.

5 The arrangement allows the formation of the electrodes and the capacitor insulating film which are excellent in coverage and prevents a broken wire in the electrode as well as a leakage current and a compositional deviation in the capacitor insulating film, thereby preventing variations in the characteristics of the capacitor element.

10 In the third method for fabricating a semiconductor device, the step of forming the capacitor element preferably includes the steps of: forming the lower electrode such that the wall surface of the opening and the bottom surface of the opening are covered with the lower electrode; forming the capacitor insulating film on the lower electrode; and forming the upper electrode on the capacitor insulating film.

In the third method for fabricating a semiconductor device, the third etching is preferably performed after removing the mask.

15 The arrangement prevents the mask from interfering with an etching gas used in the third etching and reduces a level difference produced at the wall surface of the opening through the first etching and the second etching so that the opening having a smoother wall surface is obtained.

20 In the third method for fabricating a semiconductor device, the third etching is preferably performed by using a mask having a third opening pattern formed by enlarging the opening diameter of the second opening pattern.

The arrangement reduces a level difference produced at the wall surface of the opening through the first etching and the second etching and provides the opening having a smooth wall surface.

25 Preferably, each of the second to fourth methods for fabricating semiconductor

devices further comprises, between the step of forming the mask having the first opening pattern and the step of forming the depressed portion in the insulating film, the step of: forming a wall surface of the first opening pattern into a tapered configuration.

Since the arrangement performs the first etching after forming the wall surface of the first opening pattern into a tapered configuration, the wall surface of the opening can be processed into a more tapered configuration.

In the third method for fabricating a semiconductor device, the etching stopper film is preferably composed of a metal oxide containing titanium or aluminum.

The arrangement allows the etching selectivity of the metal oxide to the conductive film to be maintained high.

A fourth method for fabricating a semiconductor device according to the present invention comprises the steps of: forming a conductive film on a specified region of a substrate; forming an insulating film on the substrate such that the conductive film is covered with the insulating film; forming, on the insulating film, a mask having a first opening pattern above the conductive film; performing first etching with respect to the insulating film by using the mask having the first opening pattern to form, in the insulating film, a depressed portion having a bottom portion not reaching the conductive film; and, after removing the mask, performing second etching with respect to an entire surface of the insulating film to form, in the insulating film, an opening for exposing the conductive film such that the opening has a diameter larger than a diameter of the depressed portion and a wall surface having a tapered configuration.

Since the fourth method for fabricating a semiconductor device forms the depressed portion not reaching the conductive film by the first etching, removes the mask, and then forms the opening by the second etching, there is no such a situation that the conductive film is adhered again to the sidewall of the mask having the first opening

pattern and a reaction product between an etching gas and the conductive film is deposited on the sidewall of the mask having the first opening pattern so that configurational abnormality, such as the formation of a fence, which has been observed in a conventional embodiment does not occur. Accordingly, the tapered configuration of the sidewall of the opening can be formed stably. In contrast to the second method for fabricating a semiconductor device, the fourth method for fabricating a semiconductor device allows the omission of the step of performing etching by using the mask having the second opening pattern obtained by enlarging the opening diameter of the first opening pattern and thereby achieves a reduction in the number of process steps.

Preferably, the fourth method for fabricating a semiconductor device further comprises the step of: forming, at least in the opening of the insulating film, a capacitor element composed of a lower electrode, a capacitor insulating film, and an upper electrode.

The arrangement allows the formation of the electrodes and the capacitor insulating film which are excellent in coverage and prevents a broken wire in the electrode as well as a leakage current and a compositional deviation in the capacitor insulating film, thereby preventing variations in the characteristics of the capacitor element.

In the fourth method for fabricating a semiconductor device, the step of forming the capacitor element preferably includes the steps of: forming the lower electrode such that the wall surface of the opening and the bottom surface of the opening are covered with the lower electrode; forming the capacitor insulating film on the lower electrode; and forming the upper electrode on the capacitor insulating film.

Preferably, the fourth method for fabricating a semiconductor device further comprises, between the step of forming the mask having the first opening pattern and the step of forming the depressed portion in the insulating film, the step of: forming a wall surface of the first opening pattern into a tapered configuration.

Since the arrangement performs the first etching after forming the wall surface of the first opening pattern into a tapered configuration, the wall surface of the opening can be processed into a more tapered configuration.

BRIEF DESCRIPTION OF THE DRAWINGS

5 FIGS. 1A to 1D are cross-sectional views each illustrating a method for fabricating a semiconductor device according to a first embodiment of the present invention;

FIGS. 2A to 2D are cross-sectional views each illustrating the method for fabricating a semiconductor device according to the first embodiment;

10 FIGS. 3A to 3C are cross-sectional views each illustrating a method for fabricating a semiconductor device according to a second embodiment of the present invention;

FIGS. 4A to 4C are cross-sectional views each illustrating the method for fabricating a semiconductor device according to the second embodiment;

15 FIG. 5A to 5C are cross-sectional views each illustrating a method for fabricating a semiconductor device according to a third embodiment of the present invention;

FIGS. 6A to 6D are cross-sectional views each illustrating the method for fabricating a semiconductor device according to the third embodiment;

20 FIG. 7A and 7B are cross-sectional views each illustrating a method for fabricating a semiconductor device according to a fourth embodiment of the present invention;

FIGS. 8A and 8B are cross-sectional views each illustrating the method for fabricating a semiconductor device according to the fourth embodiment;

25 FIG. 9A to 9C are cross-sectional views each illustrating a method for fabricating a semiconductor device according to a fifth embodiment of the present invention;

FIGS. 10A to 10C are cross-sectional views each illustrating the method for fabricating a semiconductor device according to the fifth embodiment;

FIG. 11 is a plan view of a cell block in a semiconductor device according to a sixth embodiment of the present invention;

5 FIGS. 12A to 12C are cross-sectional views each illustrating a method for fabricating the semiconductor device according to the sixth embodiment;

FIGS. 13A and 13B are cross-sectional views each illustrating the method for fabricating the semiconductor device according to the sixth embodiment;

10 FIGS. 14A and 14B are cross-sectional views each illustrating the method for fabricating the semiconductor device according to the sixth embodiment;

FIG. 15 is a cross-sectional view illustrating the method for fabricating the semiconductor device according to the sixth embodiment;

FIGS. 16A to 16C are cross-sectional views each illustrating a conventional method for fabricating a semiconductor device; and

15 FIGS. 17A to 17C are cross-sectional views each illustrating the conventional method for fabricating a semiconductor device.

DETAILED DESCRIPTION OF THE INVENTION

EMBODIMENT 1

20 A method for fabricating a semiconductor device according to a first embodiment of the present invention will be described with reference to FIGS. 1A to 1D and FIGS. 2A to 2D.

First, as shown in FIG. 1A, a first silicon oxide film 101 with a thickness of 1000 nm is formed by CVD on a semiconductor substrate 100. Then, the first silicon oxide film 101 is planarized by CMP till the thickness thereof becomes 500 nm. Subsequently, 25 selective dry etching is performed with respect to the first silicon oxide film 101, thereby

forming a contact hole having a diameter of 250 nm and connecting to the upper surface of the semiconductor substrate **100**. Then, a titanium film with a thickness of 10 nm and a titanium nitride film with a thickness of 20 nm are formed successively over the first silicon oxide film **101** and in the contact hole and a tungsten film with a thickness of 200 nm is further formed by CVD.

Next, a metal film composed of the titanium film, the titanium nitride film, and the tungsten film is left only in the contact hole by CMP to form a plug **102**. Then, by sputtering, a titanium-aluminum nitride film with a thickness of 100 nm, an iridium film with a thickness of 50 nm, and an iridium oxide film with a thickness of 100 nm are stacked successively in layers over the first silicon oxide film **101** and the plug **102**, thereby forming a multilayer film. Subsequently, selective dry etching is performed with respect to the multilayer film, thereby forming an oxygen barrier film **103** covering the plug **102**.

Here, the oxygen barrier film **103** is a conductive film.

In addition, although the case where the oxygen barrier film **103** is a conductive film is explained in this embodiment, this invention is not limited to such composition.

Next, as shown in FIG. **1B**, a second silicon oxide film **104** with a thickness of 1000 nm is formed on the first silicon oxide film **101** in such a manner as to cover the oxygen barrier film **103**. Then, the second silicon oxide film **104** is planarized by CMP till the film thickness above the oxygen barrier film **103** becomes 600 nm.

Next, as shown in FIG. **1C**, a resist mask **105** having a first opening pattern **105a** having a thickness of 700 nm above the oxygen barrier film **103** and an opening diameter of 300 nm is formed on the second silicon oxide film **104**.

Next, as shown in FIG. **1D**, first etching is performed with respect to the second silicon oxide film **104** by using the resist mask **105** having the first opening pattern **105a**

and a plasma composed of a gas mixture of a gas containing C, H, and F and a gas containing O, thereby forming a depressed portion **104a** at a depth of about 300 nm. At this time, the film thickness of the resist mask **105** is reduced to about 500 nm by the first etching.

5 Next, as shown in FIG. **2A**, etching is performed with respect to the entire surface by using a plasma composed of a gas containing O to remove the portion of the resist mask **105** corresponding to a thickness of about 300 nm and thereby form the resist mask **105** having a second opening pattern **105b** with an opening diameter of 400 nm. At this time, the wall surface of the second opening pattern **105b** is formed into a downwardly tapered
10 configuration because an upper portion of the resist mask **105** having the second opening pattern **105b** is exposed more frequently to the plasma.

Next, as shown in FIG. **2B**, second etching is performed with respect to the second silicon oxide film **104** having the depressed portion **104a** by using the resist mask **105** having the second opening pattern **105b** and a plasma composed of a gas mixture of a gas
15 containing C, H, and F and a gas containing O, thereby forming an opening **104b** for exposing the oxygen barrier film **103**. The opening **104b** has a diameter larger than that of the depressed portion **104a** and a wall surface having a tapered configuration. In this case, the film thickness of the resist mask **105** is reduced to about 100 nm by the second etching, while the oxygen barrier film **103** is over etched by a thickness of about 30 nm.

20 Thus, the opening **104b** is formed by the second etching after the depressed portion **104a** is formed by the first etching so that, if the second etching is 100% anisotropic, a stepped portion is formed in the wall surface of the opening **104b**. However, since the second etching is performed by using the resist mask **105** having the second opening pattern **105b** obtained by enlarging the opening diameter of the first opening
25 pattern **105a**, the stepped portion is partly scraped off so that it presents a gently sloped

configuration as shown in FIG. 2B. In addition, the tapered configuration of the second opening pattern 105b, which is transferred to the second silicon oxide film 104, also exerts an extra effect so that the opening 104b having a tapered wall surface is formed in the second silicon oxide film 104. An obtuse angle may be formed appropriately between the wall surface of the opening 104b and the bottom surface thereof. The opening 104b is formed such that the wall surface thereof downwardly tapers from the top portion thereof toward the bottom portion thereof, i.e., such that the diameter of the opening 104b increases gradually from the bottom portion with approach toward the top portion.

Next, as shown in FIG. 2C, the resist mask 105 is removed by ashing using a plasma composed of a gas containing O.

Next, as shown in FIG. 2D, a first platinum film with a thickness of 50 nm is formed by sputtering on the second silicon oxide film 104 including the inside of the opening 104b. Then, selective dry etching is performed with respect to the first platinum film in a region including the opening 104b, thereby forming a lower electrode 106 composed of the patterned first platinum film. Subsequently, a ferroelectric film composed of a bismuth layer-structured Perovskite-type oxide the components of which are strontium, bismuth, tantalum, and niobium is formed by MOCVD to a thickness of 50 nm over the second silicon oxide film 104 and the lower electrode 106. After a second platinum film with a thickness of 50 nm is then formed by sputtering on the ferroelectric film, the ferroelectric film and the second platinum film are patterned in a region including the lower electrode 106, whereby a capacitor insulating film 107 and an upper electrode 108 are formed. Thereafter, wiring, a protective film, and the like are formed on the capacitor, though they are not disclosed.

Thus, in accordance with the method for fabricating a semiconductor device according to the first embodiment, the depressed portion 104a is formed by the first

etching using the resist mask **105** having the first opening pattern **105a** and then the second etching is performed by using the resist mask **105** having the second opening pattern **105b** having an opening diameter larger than that of the first opening pattern **105a**. This allows the wall surface of the opening **104b** formed in the second silicon oxide film **104** to be
5 formed into a tapered configuration.

Since the oxygen barrier film **103** is prevented from being exposed when the depressed portion **104a** is formed by the first etching, there is no such a situation that the iridium oxide in the upper layer of the multilayer film composing the oxygen barrier film **103** is adhered again to the sidewall of the resist mask **105** or a reaction product between
10 fluorine and iridium is deposited on the sidewall of the resist mask **105** so that configurational abnormality, such as the formation of a fence, as has been observed in the conventional embodiment does not occur. This allows stable formation of the tapered configuration of the wall surface of the opening **104b**.

Since the tapered configuration of the wall surface of the opening **104b** can be
15 formed stably, the resultant lower electrode **106**, capacitor insulating film **107**, and upper electrode **108** are excellent in coverage so that a broken wire in the electrode as well as a leakage current and a compositional deviation in the capacitor insulating film is prevented and variations in the characteristics of the capacitor are thereby prevented.

If a metal containing iridium, platinum, gold, ruthenium, rhodium, or palladium as
20 a refractory metal or a metal oxide thereof is used in the upper layer of the multilayer film composing the oxygen barrier metal **103** or if titanium, titanium-aluminum, tantalum, tantalum-aluminum, a nitride thereof, or a multilayer film composed thereof is used in the upper layer of the multilayer film composing the oxygen barrier metal **103**, the re-adhesion
of the oxygen barrier film **103** removed by the second etching to the sidewall of the resist
25 mask **105** can be suppressed and the deposition of a reaction product between an etching

gas and the oxygen barrier film 103 on the sidewall of the resist mask 105 can also be suppressed.

Since the oxygen barrier film 103 connected to the semiconductor substrate 100 via the plug 102 is used as the underlying film of the lower electrode 106, the plug 102 is
5 no more oxidized during the formation of the capacitor composed of a ferroelectric film or a high dielectric film, which allows a connection between the capacitor and the semiconductor substrate 100.

Since the second silicon oxide film 104 is an oxide film containing silicon as a main component, highly anisotropic etching can be performed with respect to the second
10 silicon oxide film 104. By forming the opening 104b by the second etching after the formation of the depressed portion 104a by the first etching, the stepped portion in the wall surface of the opening 104b is reduced in level and a smoothly tapered configuration is obtained.

In addition, the planarization of the principal surface of the second silicon oxide
15 film 104 reduces a focus shift in the resist mask 105 used in forming the capacitor element composed of the electrodes and the capacitor insulating film or a high dielectric film.

Since the resist mask 105 composed of a photoresist film is used as the mask, the etching selectivity of the resist mask 105 to the insulating film can be maintained sufficiently high.

20 Since the first etching is performed by using the plasma containing the oxygen gas, the etching selectivity of the resist mask 105 to the second silicon oxide film 104 can also be maintained sufficiently high.

Although the present embodiment has described the case where the capacitor is formed in the opening 104b, the present embodiment is not limited to the formation of the
25 capacitor. Another element may also be formed instead.

EMBODIMENT 2

A method for fabricating a semiconductor device according to a second embodiment of the present invention will be described with reference to FIGS. 3A to 3C and FIGS. 4A to 4C.

5 First, as shown in FIG. 3A, a first silicon oxide film 201, a plug 202, an oxygen barrier film 203, a second silicon oxide film 204, and a resist mask 205 having a first opening pattern 205a having a thickness of 700 nm and an opening diameter of 300 nm are formed on a semiconductor substrate 200 in the same manner as in the description given with respect to FIGS. 1A to 1C in the first embodiment.

10 Next, as shown in FIG. 3B, first etching is performed with respect to the second silicon oxide film 204 by using the resist mask 205 having the first opening pattern 205a and a plasma composed of a gas mixture of a gas containing C, H, and F and a gas containing O, thereby forming a depressed portion 204a at a depth of about 300 nm. In this case, the film thickness of the resist mask 205 is reduced to about 500 nm by the first
15 etching.

Next, as shown in FIG. 3C, etching using a plasma composed of a gas containing O is performed with respect to the entire surface, thereby removing the portion of the photoresist 205 corresponding to a thickness of about 300 nm and forming the resist mask 205 having a second opening pattern 205b having an opening diameter of 400 nm which is
20 obtained by enlarging the opening diameter of the first opening pattern 205a. At this time, the cross section of the second opening pattern 205b is formed into a downwardly tapered configuration because an upper portion of the resist mask 205 having the second opening pattern 205b is more frequently exposed to the plasma.

Next, as shown in FIG. 4A, second etching is performed with respect to the
25 second silicon oxide film 204 having the depressed portion 204a by using the resist mask

205 having the second opening pattern **205b** and a plasma composed of a gas mixture of a gas containing C, H, and F and a gas containing O, thereby forming an opening **204b** for exposing the oxygen barrier film **203**. The opening **204b** has a diameter larger than that of the depressed portion **204a** and a wall surface having a tapered configuration. In this case, the film thickness of the resist mask **205** is reduced to about 100 nm by the second etching, while the oxygen barrier film **203** is over etched by a thickness of about 30 nm.

Thus, the opening **204b** is formed by the second etching after the depressed portion **204a** is formed by the first etching so that, if the second etching is 100% anisotropic, a stepped portion is formed in the wall surface of the opening **204b**. However, since the second etching is performed by using having the second opening pattern **205b** obtained by enlarging the opening diameter of the first opening pattern **205a**, the stepped portion is partly scraped off so that it presents a gently sloped configuration as shown in FIG. 4A. In addition, the tapered configuration of the second opening pattern **205b**, which is transferred to the second silicon oxide film **204**, also exerts an extra effect so that the opening **204b** having a tapered wall surface is formed in the second silicon oxide film **204**.

Next, as shown in FIG. 4B, the resist mask **205** is removed by ashing using a plasma composed of a gas containing O.

Next, as shown in FIG. 4C, third etching is performed entirely with respect to the second silicon oxide film **204** and the oxygen barrier film **203** exposed in the opening **204b** without using a mask, thereby further reducing a level difference at the wall surface of the opening **204b**. In this case, the oxygen barrier film **203** is over etched by a thickness of about 50 nm. Then, a lower electrode, a capacitor insulating film, and an upper electrode are formed in the same manner as in the first embodiment. Thereafter, wiring, a protective film, and the like are formed on the capacitor, though they are not disclosed.

Thus, in accordance with the method for fabricating a semiconductor device

according to the second embodiment, the depressed portion **204a** is formed by the first etching using the resist mask **205** having the first opening pattern **205a** and then the second etching is performed by using the resist mask **205** having the second opening pattern **205b** having an opening diameter larger than that of the first opening pattern **205a**. This allows
5 the wall surface of the opening **204b** formed in the second silicon oxide film **204** to be formed into a downwardly tapered configuration.

Since the oxygen barrier film **203** is prevented from being exposed when the depressed portion **204a** is formed by the first etching, there is no such a situation that the iridium oxide in the upper layer of the multilayer film composing the oxygen barrier film
10 **203** is adhered again to the sidewall of the resist mask **205** or a reaction product between fluorine and iridium is deposited on the sidewall of the resist mask **205** so that configurational abnormality, such as the formation of a fence, as has been observed in the conventional embodiment does not occur. This allows stable formation of the tapered configuration of the wall surface of the opening **204b**.

15 Since the third etching is performed with respect to the second silicon oxide film **204** having the opening **204b** in which the oxygen barrier film **203** is exposed after the step of removing the resist mask **205** by ashing, the etching gas used in performing the third etching reaches the opening **204b** without being interrupted by the mask so that the wall surface of the opening **204b** formed after the first etching and the second etching are
20 performed has a reduced level difference and a more smoothly tapered configuration. As a result, a lower electrode, a capacitor insulating film, and an upper electrode, which are more excellent in coverage, are obtainable so that a broken wire in the electrode as well as a leakage current and a compositional deviation in the capacitor insulating film is prevented and variations in the characteristics of the capacitor are thereby prevented.

25 Although the present embodiment has described the case where the third etching

is performed with respect to the second silicon oxide film **204** having the opening **204b** in which the oxygen barrier film **203** is exposed after the step of removing the resist mask **205** by ashing, the third etching may also be performed by using the resist mask **205** having an opening pattern obtained by enlarging the opening diameter of the second opening pattern **205b**. In this case also, it will easily be appreciated that the wall surface of the opening **204b** having a more smoothly tapered configuration is obtainable after the second etching.

If a metal containing iridium, platinum, gold, ruthenium, rhodium, or palladium as a refractory metal or a metal oxide thereof is used in the upper layer of the multilayer film composing the oxygen barrier metal **203** or if titanium, titanium-aluminum, tantalum, tantalum-aluminum, a nitride thereof, or a multilayer film composed thereof is used in the upper layer of the multilayer film composing the oxygen barrier metal **203**, the re-adhesion of the oxygen barrier film **203** removed by the second etching to the sidewall of the resist mask **205** can be suppressed and the deposition of a reaction product between an etching gas and the oxygen barrier film **203** on the sidewall of the resist mask **205** can also be suppressed.

Since the oxygen barrier film **203** connected to the semiconductor substrate **200** via the plug **202** is used as the underlying film of the lower electrode, the plug **202** is no more oxidized during the formation of the capacitor insulating film composed of a ferroelectric film or a high dielectric film, which allows a connection between the capacitor and the semiconductor substrate **200**.

Since the second silicon oxide film **204** is an oxide film containing silicon as a main component, highly anisotropic etching can be performed with respect to the second silicon oxide film **204**. By forming the opening **204b** by the second etching after the formation of the depressed portion **204a** by the first etching, therefore, the stepped portion

in the wall surface of the opening **204b** is reduced in level and a smoothly tapered configuration is obtained.

In addition, the planarization of the principal surface of the second silicon oxide film **204** reduces a focus shift in the resist mask **205** used in forming the capacitor
5 composed of the electrodes and the capacitor insulating film or a high dielectric film.

Since the resist mask **205** composed of a photoresist film is used as the mask, the etching selectivity of the resist mask **205** to the insulating film can be maintained sufficiently high.

Since the first etching is performed by using the plasma containing an oxygen gas,
10 the etching selectivity of the resist mask **205** to the second silicon oxide film **204** can also be maintained sufficiently high.

Although the present embodiment has described the case where the capacitor is formed in the opening, the present embodiment is not limited to the formation of the capacitor. Another element may also be formed instead.

15 EMBODIMENT 3

A method for fabricating a semiconductor device according to a third embodiment of the present invention will be described with reference to FIGS. **5A** to **5C** and FIGS. **6A** to **6C**.

First, as shown in FIG. **5A**, a first silicon oxide film **301**, a plug **302**, and an
20 oxygen barrier film **303** are formed on a semiconductor substrate **300** in the same manner as in the description given with respect to FIG. **1A** in the first embodiment. Then, an etching stopper film **304** composed of an aluminum titanium oxide and having a thickness of 50 nm is formed on the oxygen barrier film **303**.

Next, a second silicon oxide film **305** and a resist mask **306** having a first opening
25 pattern **306a** having a thickness of 700 nm and an opening diameter of 300 nm are formed

in the same manner as in the description given with respect to FIGS. 1B and 1C in the first embodiment.

Next, as shown in FIG. 5C, first etching is performed with respect to the second silicon oxide film 305 by using the resist mask 306 having the first opening pattern 306a and a plasma composed of a gas mixture of a gas containing C, H, and F and a gas containing O, thereby forming a depressed portion 305a at a depth of about 300 nm. At this time, the film thickness of the resist mask 306 is reduced to about 500 nm by the first etching.

Next, as shown in FIG. 6A, etching using a plasma composed of a gas containing O is performed with respect to the entire surface, thereby removing the portion of the photoresist 306 corresponding to a thickness of about 300 nm and forming the resist film 306 having a second opening pattern 306b having an opening diameter of 400 nm. At this time, the cross section of the second opening pattern 306b is formed into a downwardly tapered configuration because an upper portion of the resist mask 306 having the second opening pattern 306b is more frequently exposed to the plasma.

Next, as shown in FIG. 6B, second etching is performed with respect to the second silicon oxide film 305 having the depressed portion 305a by using the resist mask 306 having the second opening pattern 306b and a plasma composed of a gas mixture of a gas containing C, H, and F and a gas containing O, thereby forming an opening 305b for exposing the etching stopper film 304. The opening 305b has a diameter larger than that of the depressed portion 305a and a wall surface having a tapered configuration. In this case, the film thickness of the resist mask 306 is reduced to about 100 nm by the second etching, while the etching stopper film 304 is over etched by a thickness of about 30 nm.

Thus, the opening 305b is formed by the second etching after the depressed portion 305a is formed by the first etching so that, if the second etching is 100%

anisotropic, a stepped portion is formed at the wall surface of the opening **305b**. However, since the second etching is performed by using the mask having the second opening pattern **306b** obtained by enlarging the opening diameter of the first opening pattern **306a**, the stepped portion is partly scraped off so that it presents a gently sloped configuration as shown in FIG. **6B**. In addition, the tapered configuration of the second opening pattern **306b**, which is transferred to the second silicon oxide film **305**, also exerts an extra effect so that the opening **305b** having a tapered wall surface is formed in the second silicon oxide film **305**.

Next, as shown in FIG. **6C**, the photoresist **306** is removed by ashing using a plasma composed of a gas containing O.

Next, as shown in FIG. **6D**, third etching is performed by sputtering with respect to the entire surface of the second silicon oxide film **305** having the opening **305b** in which the etching stopper film **304** is exposed without using a mask, thereby further reducing a level difference at the wall surface of the opening **305b**. By the third etching, the opening **305b** penetrates the etching stopper film **304** to expose the oxygen barrier film **303**. On the other hand, the oxygen barrier film **303** is over etched by a thickness of about 10 nm. Then, a lower electrode, a capacitor insulating film, and an upper electrode are formed in the same manner as in the first embodiment. Thereafter, wiring, a protective film, and the like are formed, though they are not disclosed.

Thus, in accordance with the method for fabricating a semiconductor device according to the third embodiment, the depressed portion **305a** is formed by the first etching using the resist mask **306** having the first opening pattern **306a** and then the second etching is performed by using the resist mask **306** having the second opening pattern **306b** having an opening diameter larger than that of the first opening pattern **306a**. This allows the wall surface of the opening **305b** formed in the second silicon oxide film **305** to be

formed into a downwardly tapered configuration.

Since the oxygen barrier film **303** is prevented from being exposed when the depressed portion **305a** is formed by the first etching, there is no such a situation that the iridium oxide in the upper layer of the multilayer film composing the oxygen barrier film **303** is adhered again to the sidewall of the resist mask **306** or a reaction product between fluorine and iridium is deposited on the sidewall of the resist mask **306** so that configurational abnormality, such as the formation of a fence, as has been observed in the conventional embodiment does not occur. This allows stable formation of the tapered configuration of the wall surface of the opening **305b**.

10 In addition, the etching stopper film **304** formed on the oxygen barrier film **303** prevents the oxygen barrier film **303** from being exposed in the opening **305b** formed by the second etching. This allows the wall surface of the opening **305b** to have a more smoothly tapered configuration through the third etching and suppresses an amount of over etching performed with respect to the oxygen barrier film **303** during the third etching. As
15 a result, a lower electrode, a capacitor insulating film, and an upper electrode, which are more excellent in coverage, are obtainable so that a broken wire in the electrode as well as a leakage current and a compositional deviation in the capacitor insulating film is prevented and variations in the characteristics of the capacitor are thereby prevented. In addition, the oxygen barrier film **303** is allowed to have a sufficiently large thickness so
20 that a semiconductor device excellent in barrier property is fabricated.

By using an oxide containing titanium or aluminum, which is a low-melting metal, in the etching stopper film **304**, the etching selectivity of the etching stopper film **304** to the oxide of iridium, which is a refractory metal in the upper layer of the multilayer film composing the oxygen barrier film **303** as the underlying film of the etching stopper film
25 **304**, can be maintained high.

Although the present embodiment has described the case where the third etching is performed with respect to the second silicon oxide film **305** having the opening **305b** in which the etching stopper film **304** is exposed after the step of removing the resist mask **305** by ashing, the third etching may also be performed by using the resist mask **306** having an opening pattern obtained by enlarging the opening diameter of the second opening pattern **306b**. In this case also, it will easily be appreciated that the wall surface of the opening **305b** having a more smoothly tapered configuration is obtainable after the second etching.

Although the present embodiment has described the case where the third etching is performed with respect to the second silicon oxide film **305** having the opening **305b** in which the oxygen barrier film **303** is exposed after the step of removing the resist mask **306** by ashing, the third etching may also be performed by using the resist mask **306** having an opening pattern obtained by enlarging the opening diameter of the second opening pattern **306b**. In this case also, it will easily be appreciated that the wall surface of the opening **305b** with a more smoothly tapered configuration is obtainable after the second etching. In this case, if a metal containing iridium, platinum, gold, ruthenium, rhodium, or palladium as a refractory metal or a metal oxide thereof is used in the upper layer of the multilayer film composing the oxygen barrier metal **303** or if titanium, titanium-aluminum, tantalum, tantalum-aluminum, a nitride thereof, or a multilayer film composed thereof is used in the upper layer of the multilayer film composing the oxygen barrier metal **303**, the re-adhesion of the oxygen barrier film **303** removed by the third etching to the resist mask **306** can be suppressed and the deposition of a reaction product between an etching gas and the oxygen barrier film **303** on the resist mask **306** can also be suppressed.

Since the oxygen barrier film **303** connected to the semiconductor substrate **300**

via the plug 302 is used as the underlying film of the lower electrode, the plug 302 is no more oxidized during the formation of the capacitor insulating film composed of a ferroelectric film or a high dielectric film, which allows a connection between the capacitor and the semiconductor substrate 300.

5 Since the second silicon oxide film 305 is an oxide film containing silicon as a main component, highly anisotropic etching can be performed with respect to the second silicon oxide film 305. By forming the opening 305b by the second etching after the formation of the depressed portion 305a by the first etching, therefore, the stepped portion at the wall surface of the opening 305b is reduced in level and a smoothly tapered
10 configuration is obtained.

 In addition, the planarization of the principal surface of the second silicon oxide film 305 reduces a focus shift in the resist mask 306 used in forming the capacitor composed of the electrodes and the capacitor insulating film or a high dielectric film.

 Since the resist mask 306 composed of a photoresist film is used as the mask, the
15 etching selectivity to the resist mask 306 can be maintained sufficiently high.

 Since the first etching is performed by using the plasma containing an oxygen gas, the etching selectivity of the resist mask 306 to the second silicon oxide film 305 can also be maintained sufficiently high.

 Although the present embodiment has described the case where the capacitor is
20 formed in the opening, the present embodiment is not limited to the formation of the capacitor. Another element may also be formed instead.

EMBODIMENT 4

 A method for fabricating a semiconductor device according to a fourth
embodiment of the present invention will be described with reference to FIGS. 7A and 7B
25 and FIGS. 8A and 8B.

First, as shown in FIG. 7A, a first silicon oxide film 401, a plug 402, and an oxygen barrier film 403 are formed on a semiconductor substrate 400 in the same manner as in the description given with respect to FIGS. 1A to 1C in the first embodiment. Then, a second silicon oxide film 404 is formed over the first silicon oxide film 401 and the oxygen barrier film 403 in such a manner as to cover the oxygen barrier film 403. Subsequently, the second silicon oxide film 404 on the oxygen barrier film 403 is planarized by CMP till the thickness of the second silicon oxide film 404 becomes 900 nm. Then, a resist mask 405 having an opening pattern 405a having a thickness of 700 nm and an opening diameter of 300 nm is formed on the second silicon oxide film 404.

Next, as shown in FIG. 7B, first etching is performed by using the resist mask 405 having the opening pattern 405a and a plasma composed of a gas mixture of a gas containing C, H, and F and a gas containing O, thereby forming a depressed portion 404a at a depth of about 600 nm. In this case, the film thickness of the resist mask 405 is reduced to about 500 nm by the first etching.

Next, as shown in FIG. 8A, the resist mask 405 is removed by ashing using a plasma composed of a gas containing O.

Next, as shown in FIG. 8B, second etching is performed with respect to the second silicon oxide film 404 having the depressed portion 404a without using a mask and by using a plasma composed of a gas mixture of a gas containing C, H, and F and a gas containing O, thereby forming an opening 404b in which the oxygen barrier film 403 is exposed. The opening 404b has a diameter larger than that of the depressed portion 404a and a wall surface having a tapered configuration. In the mean time, the oxygen barrier film 403 is over etched by a thickness of about 30 nm. Then, a lower electrode, a capacitor insulating film, and an upper electrode are formed in the same manner as in the first embodiment. Thereafter, wiring, a protective film, and the like are formed, though they are

not disclosed.

Thus, in accordance with the method for fabricating a semiconductor device according to the fourth embodiment, the step of enlarging the diameter of the opening pattern can be omitted so that the number of process steps is reduced compared with that in
5 the first embodiment.

In addition, the depressed portion **404a** is formed by the first etching using the resist mask **405** having the first opening pattern **405a** and then the second etching is performed after removing the resist mask **405** by ashing. This allows the wall surface of the opening **404b** formed in the second silicon oxide film **404** to be formed into a
10 downwardly tapered configuration.

Since the oxygen barrier film **403** is prevented from being exposed when the depressed portion **404a** is formed by the first etching, there is no such a situation that the iridium oxide in the upper layer of the multilayer film composing the oxygen barrier film **403** is adhered again to the sidewall of the resist mask **405** or a reaction product between
15 fluorine and iridium is deposited on the sidewall of the resist mask **405** so that configurational abnormality, such as the formation of a fence, as has been observed in the conventional embodiment does not occur. This allows stable formation of the tapered configuration of the wall surface of the opening **404b**. As a result, a lower electrode, a capacitor insulating film, and an upper electrode, which are more excellent in coverage, are
20 obtainable so that a broken wire in the electrode as well as a leakage current and a compositional deviation in the capacitor insulating film is prevented and variations in the characteristics of the capacitor are thereby prevented.

Since the oxygen barrier film **403** connected to the semiconductor substrate **400** via the plug **402** is used as the underlying film of the lower electrode, the plug **402** is no
25 more oxidized during the formation of the capacitor insulating film composed of a

ferroelectric film or a high dielectric film, which allows a connection between the capacitor and the semiconductor substrate **400**.

Since the second silicon oxide film **404** is an oxide film containing silicon as a main component, highly anisotropic etching can be performed with respect to the second silicon oxide film **404**. By forming the opening **404b** by the second etching after the formation of the depressed portion **404a** by the first etching, therefore, the stepped portion at the wall surface of the opening **404b** is reduced in level and a smoothly tapered configuration is obtained.

In addition, the planarization of the principal surface of the second silicon oxide film **404** reduces a focus shift in the resist mask **405** used in forming the capacitor composed of the electrodes and the capacitor insulating film or a high dielectric film.

Since the resist mask **405** composed of a photoresist film is used as the mask, the etching selectivity of the resist mask **405** to the insulating film can be maintained sufficiently high.

Since the first etching is performed by using the plasma containing an oxygen gas, the etching selectivity of the resist mask **405** to the second silicon oxide film **404** can also be maintained sufficiently high.

Although the present embodiment has described the case where the capacitor is formed in the opening **404b**, the present embodiment is not limited to the formation of the capacitor. Another element may also be formed instead.

EMBODIMENT 5

A method for fabricating a semiconductor device according to a fifth embodiment of the present invention will be described with reference to FIGS. **9A** to **9C** and FIGS. **10A** to **10C**.

First, as shown in FIG. **9A**, a first silicon oxide film **501**, a plug **502**, an oxygen

barrier film 503, a second silicon oxide film 504, and a resist mask 505 having a first opening pattern 505a with a thickness of 800 nm and an opening diameter of 250 nm are formed on a semiconductor substrate 500 in the same manner as in the description given with respect to FIGS. 1A to 1C in the first embodiment.

5 Next, as shown in FIG. 9B, etching using a plasma composed of a gas containing O is performed with respect to the entire surface, thereby removing the portion of the resist mask 505 corresponding to a thickness of about 100 nm and forming the resist mask 505 having a second opening pattern 505b with a diameter of 300 nm. At this time, the cross section of the second opening pattern 505b is formed into a downwardly tapered configuration because an upper portion of the resist mask 505 having the second opening
10 pattern 505b is more frequently exposed to the plasma.

Next, as shown in FIG. 9C, first etching is performed with respect to the second silicon oxide film 504 by using the resist mask 505 having the second opening pattern 505b and a plasma composed of a gas mixture of a gas containing C, H, and F and a gas
15 containing O, thereby forming a depressed portion 504b at a depth of about 300 nm. In this case, the film thickness of the resist mask 505 is reduced to about 500 nm by the first etching, while the tapered configuration of the second opening pattern 505b is transferred to the silicon oxide film 504. This achieves the effect of forming the depressed portion 504a having a tapered wall surface in the silicon oxide film 504.

20 Next, as shown in FIG. 10A, the resist mask 505 is partly removed by a thickness of about 300 nm by using a plasma composed of a gas containing O, thereby forming the resist mask 505 having a third opening pattern 505c having an opening diameter of 400 nm.

Next, as shown in FIG. 10B, second etching is performed with respect to the second silicon oxide film 504 formed with the depressed portion 504a by using the resist
25 mask 505 having the third opening pattern 505c and a plasma composed of a gas mixture

of a gas containing C, H, and F and a gas containing O, thereby forming an opening **504b** for exposing the oxygen barrier film **503**. The opening **504b** has a diameter larger than that of the depressed portion **504a** and a wall surface having a tapered configuration. In this case, the film thickness of the resist mask **505** is reduced to about 100 nm by the third etching, while the oxygen barrier film **503** is over etched by a thickness of about 30 nm. Since the second etching is performed with respect to the depressed portion **504a** having a tapered wall surface formed by the first etching, a stepped portion at the wall surface of the opening **504b** formed by the second etching is reduced in level so that the wall surface of the opening **504b** is more gently sloped than the wall surface of the opening **104b** formed in the first embodiment.

Next, as shown in FIG. **10C**, the resist mask **505** is removed by ashing using a plasma composed of a gas containing O. Then, a lower electrode, a capacitor insulating film, and an upper electrode are formed in the same manner as in the first embodiment. Thereafter, wiring, a protective film, and the like are formed, though they are not disclosed.

Thus, since the method for fabricating a semiconductor device according to the fifth embodiment includes the step of forming the opening pattern of the resist mask **505** into a tapered configuration before performing the first etching, the speed at which the second silicon oxide film **504** is removed by the first etching is increased so that an amount of tapering at the wall surface of the depressed portion **504a** formed by the first etching is increased compared with that in any of the foregoing embodiments. Since the amount of tapering at the wall surface of the depressed portion **504a** is large, the etching gas used in the second etching more easily enters the depressed portion **504a** so that the opening **504b** having the tapered wall surface with a larger amount of tapering is formed successfully. This allows the formation of a capacitor more excellent in coverage.

Since the oxygen barrier film **503** is prevented from being exposed when the

depressed portion 504a is formed by the first etching, there is no such a situation that the iridium oxide in the upper layer of the multilayer film composing the oxygen barrier film 503 is adhered again to the sidewall of the resist mask 505 or a reaction product between fluorine and iridium is deposited on the sidewall of the resist mask 505 so that
5 configurational abnormality, such as the formation of a fence, as has been observed in the conventional embodiment does not occur. This allows stable formation of the tapered configuration of the wall surface of the opening 504b.

In addition, the tapered configuration of the wall surface of the opening 504b can be formed stably. As a result, a lower electrode, a capacitor insulating film, and an upper
10 electrode, which are more excellent in coverage, are obtainable so that a broken wire in the electrode as well as a leakage current and a compositional deviation in the capacitor insulating film is prevented and variations in the characteristics of the capacitor are thereby prevented.

If a metal containing iridium, platinum, gold, ruthenium, rhodium, or palladium as
15 a refractory metal or a metal oxide thereof is used in the upper layer of the multilayer film composing the oxygen barrier metal 503 or if titanium, titanium-aluminum, tantalum, tantalum-aluminum, a nitride thereof, or a multilayer film composed thereof is used in the upper layer of the multilayer film composing the oxygen barrier metal 503, the re-adhesion of the oxygen barrier film 503 removed by the second etching to the sidewall of the resist
20 mask 505 can be suppressed and the deposition of a reaction product between an etching gas and the oxygen barrier film 503 on the sidewall of the resist mask 505 can also be suppressed.

Since the oxygen barrier film 503 connected to the semiconductor substrate 500 via the plug 502 is used as the underlying film of the lower electrode, the plug 502 is no
25 more oxidized during the formation of the capacitor composed of a ferroelectric film or a

high dielectric film, which allows a connection between the capacitor and the semiconductor substrate **500**.

Since the second silicon oxide film **504** is an oxide film containing silicon as a main component, highly anisotropic etching can be performed with respect to the second silicon oxide film **504**. By forming the opening **504b** by the second etching after the formation of the depressed portion **504a** by the first etching, therefore, the stepped portion at the wall surface of the opening **504b** is reduced in level and a smoothly tapered configuration is obtained.

In addition, the planarization of the principal surface of the second silicon oxide film **504** reduces a focus shift in the resist mask **505** used in forming the capacitor composed of the electrodes and the capacitor insulating film or a high dielectric film.

Since the resist mask **505** composed of a photoresist film is used as the mask, the etching selectivity of the resist mask **505** to the insulating film can be maintained sufficiently high.

Since the first etching is performed by using the plasma containing an oxygen gas, the etching selectivity of the resist mask **505** to the second silicon oxide film **504** can be maintained sufficiently high.

Although the present embodiment has described the case where the capacitor is formed in the opening **504b**, the present embodiment is not limited to the formation of the capacitor. Another element may also be formed instead.

EMBODIMENT 6

A semiconductor device according to a sixth embodiment of the present invention will be described with reference to FIG. 11.

FIG. 11 is a plan view of a cell block in the semiconductor device according to the sixth embodiment.

As shown in FIG. 11, an insulating lower hydrogen barrier film **618** composed of a silicon nitride is formed on a semiconductor substrate **610** composed of, e.g., silicon. A plurality of capacitors **627** arranged as a matrix are formed on the insulating lower hydrogen barrier film **618**.

5 The plurality of capacitors **627** are divided into groups each consisting of, e.g., 65 capacitors **627** arranged in a direction crossing the direction in which a bit line extends, which will be described later. The 65 capacitors **627** belonging to each of the groups have respective upper electrodes electrically connected to each other to compose a cell plate **650**. The capacitor **627A** positioned at one end portion of each of the cell plates **650** is a dummy
10 capacitor for conduction which provides an electrical connection between the semiconductor substrate **610** and the cell plate **650**. Accordingly, the number of the capacitors **627** contained in each of the cell plates **650** is substantially 64. By way of example, one cell block **660** has a configuration such that the 64 cell plates **650** are arranged in the directions in which bit lines extend.

15 By arranging, e.g., 16 cell blocks **660** in the directions in which the cell plates **650** extend, a capacitor array as a semiconductor memory device is constructed. It will easily be appreciated that the number of the capacitors **627** contained in each of the cell plates **650**, the number of the cell plates **650** contained in each of the cell blocks **660**, and the number of the cell blocks **660** contained in one capacitor array are not limited to those
20 described above.

Each of the cell blocks **660** containing the plurality of cell plates **650** is covered with an insulating upper hydrogen barrier film **629** composed of, e.g., a titanium-aluminum oxide (TiAlO) having an insulating property. The insulating upper hydrogen barrier film **629** have ends connected to the ends of the insulating lower hydrogen barrier film **618** at
25 an connecting portion **629a**. That is, the connecting portion **629a** is disposed in the

peripheral edge portion of the cell block **660**.

A description will be given herein below to a method for fabricating the semiconductor device according to the sixth embodiment with reference to FIGS. **12A** to **12C**, FIGS. **13A** and **13B**, FIGS. **14A** and **14B**, and FIG. **15**.

FIGS. **12A** to **12C**, FIGS. **13A** and **13B**, FIGS. **14A** and **14B**, and FIG. **15** are cross-sectional views illustrating the individual process steps of the method for fabricating the semiconductor device according to the sixth embodiment. It is to be noted that the cross sections shown in FIGS. **12A** to **12C**, FIGS. **13A** and **13B**, FIGS. **14A** and **14B**, and FIG. **15** are taken in directions crossing the directions in which the cell plates **650** shown in FIG. **11** extend (in the direction in which the bit lines extend). Specifically, a partial view of FIG. **14B** showing a range ended at the connecting portion **629a** and a state yet unformed with a fifth interlayer insulating film **630**, which will be described later, corresponds to a cross-sectional view taken along the line XIV(b)-XIV(b) of FIG. **11**. In FIGS. **12A** to **12C**, FIGS. **13A** and **13B**, FIGS. **14A** and **14B**, and FIG. **15**, the same reference numerals are used to denote the same components as shown in FIG. **11**. The description of the same components will not be repeated and, if the same method as used in the foregoing first embodiment is used, the description thereof will not be repeated, either.

- Formation of MOS Transistors -

First, as shown in FIG. **12A**, trenched portions each at a depth of about 300 nm are formed in the upper surface of the semiconductor substrate **610** by lithography and dry etching. Subsequently, a silicon oxide is deposited by CVD over the entire surface of the semiconductor substrate **610**. Then, the silicon oxide is removed by CMP until the surface of the semiconductor substrate **610** is exposed, whereby isolation regions **611** composed of the silicon oxide film buried in the trenched portions are formed selectively.

Next, a gate insulating film (not shown) having a thickness of about 10 nm is

formed by, e.g., thermal oxidation on the principal surface of the semiconductor substrate **610**. Subsequently, polysilicon having a film thickness of about 200 nm is deposited by low pressure CVD on the gate insulating film and then patterned by lithography and dry etching to form a plurality of gate electrodes **612** composed of the polysilicon.

5 Next, a silicon oxide having a film thickness of about 50 nm is deposited by CVD over the semiconductor substrate **610** in such a manner as to cover the gate electrodes **612** and then etched back to form sidewall insulating films (not shown) on both sides of the gate electrodes **612**.

10 Next, e.g., arsenic ions at a high concentration are implanted into the semiconductor substrate **610** by using the gate electrodes **612** and the sidewall insulating films as a mask so that drain diffusion layers **613a** and source diffusion layers **613b** are formed, whereby MOS transistors are formed. In forming the drain diffusion layers **613a** and the source diffusion layers **613b**, a diffusion layer **613c** for wiring is formed selectively in the active region of the semiconductor substrate **610** except for MOS
15 transistor formation regions.

- Formation of Bit Lines -

20 Next, as shown in FIG. 12B, a silicon oxide is deposited by CVD over the entire surface of the semiconductor substrate **610** and then planarized by CMP to have a film thickness which is about 200 nm over the gate electrodes **612**, so that a first interlayer insulating film **614** composed of the silicon oxide is formed.

25 Next, contact holes for exposing the respective surfaces of the drain diffusion layers **613a** and the diffusion layer **613c** for wiring are formed in the first interlayer insulating film **614** by lithography and dry etching. Then, a titanium film and a titanium nitride film are deposited successively by CVD on the inner walls of the contact holes such that the contact holes are not filled completely therewith. Subsequently, tungsten is filled in

the contact holes. In this manner, first contact plugs 615 each connected to the drain diffusion layer 613a or to the diffusion layer 613c for wiring are formed, as shown in FIG 12B.

Next, a multilayer film consisting of a titanium film having a thickness of about 10 nm and a tungsten film having a thickness of about 100 nm, which are stacked successively in ascending order, is formed by sputtering on the first interlayer insulating film 614. Then, the multilayer film is patterned by lithography and dry etching to form bit lines 616 connected to the first contact plugs 615, as shown in FIG 12B.

- Formation of Insulating Lower Hydrogen Barrier Film -

Next, as shown in FIG 12C, a silicon oxide is formed by CVD over the entire surface of the first interlayer insulating film 614 and then planarized by CMP to have a film thickness which is about 100 nm over the bit lines 616, so that a second interlayer insulating film 617 composed of the silicon oxide is formed.

Next, the insulating lower hydrogen barrier film 618 composed of a silicon nitride having a film thickness of about 100 nm is deposited by CVD on the second interlayer insulating film 617.

Next, contact holes extending through the insulating lower hydrogen barrier film 618, the second interlayer insulating film 617, and the first interlayer insulating film 614 to expose the upper surfaces of the source diffusion layers 613b of the MOS transistors are formed by lithography and dry etching. Then, a titanium film, a titanium nitride film, and tungsten are buried successively in the contact holes to form second contact plugs 619 connected to the source diffusion layers 613b.

Next, as shown in FIG 13A, a multilayer film composed of a titanium-aluminum nitride, iridium, and an iridium oxide each having a film thickness of about 50 nm and deposited successively by, e.g., sputtering is formed over the entire surface of the

insulating lower hydrogen barrier film 618. Then, the multilayer film is patterned by lithography and dry etching to form conductive lower hydrogen barrier films 620 composed of the titanium-aluminum nitride and oxygen barrier films 621 composed of the iridium and the iridium oxide. The conductive lower hydrogen barrier films 620 are connected to the upper ends of the second contact plugs 619 at the center portions of the lower surfaces thereof and connected to the insulating lower hydrogen barrier film 618 at the peripheral edge portions of the lower surfaces.

- Formation of Capacitors -

Next, as shown in FIG. 13B, a silicon oxide film having a thickness of 1000 nm is deposited over the entire surface of the insulating hydrogen barrier film 618 in such a manner as to cover the oxygen barrier films 621 and the conductive lower hydrogen barrier films 620. Then, the silicon oxide film is planarized by CMP to have a thickness which is 600 nm over the oxygen barrier films 621, thereby forming a third interlayer insulating film 622.

Next, a resist mask (not shown) having a first opening pattern (not shown) above each of the oxygen barrier films 621 is formed on the third interlayer insulating film 622. Then, first etching is performed by using the first opening pattern to form depressed portions (not shown) each having a depth not reaching the oxygen barrier film 621.

Next, etching is performed with respect to the entire surface of the resist mask having the first opening pattern to enlarge the opening diameter of the first opening pattern and thereby form a resist mask (not shown) having a second opening pattern (not shown) which is larger in opening diameter than the first opening pattern.

Next, second etching is performed with respect to the third interlayer insulating film 622 formed with the depressed portions by using the resist mask having the second opening pattern to form openings 623 for exposing the oxygen barrier film 621. The

openings 623 have diameters larger than those of the depressed portions and tapered wall surfaces.

Thus, the openings 623 are formed by forming the depressed portions by the first etching and then performing the second etching with respect to the depressed portions.

5 Consequently, a level difference at the wall surface of each of the openings 623 is reduced, as shown in FIG. 13B.

The process steps in the present embodiment are the same as those illustrated in detail in the first embodiment until the formation of the openings 623 is completed.

Next, as shown in FIG. 14A, an iridium oxide having a film thickness of about 5
10 nm and platinum having a film thickness of about 50 nm are deposited successively by sputtering over the entire surface of the third interlayer insulating film 622 including the wall and bottom surfaces of the openings 623. The deposited films are then patterned by lithography and dry etching such that at least the portions thereof formed in the openings 623 are left, thereby forming lower electrodes 624 each composed of the iridium oxide and
15 the platinum.

Next, a ferroelectric film composed of a bismuth layer-structured Perovskite-type oxide, having a thickness of about 50 nm, and serving as capacitor insulating films 625 is deposited by metal organic chemical vapor deposition (MOCVD) over the entire surface of the third interlayer insulating film 622 including the openings 623 formed with the lower
20 electrodes 624. The ferroelectric film contains strontium, bismuth, tantalum, or niobium as a main component.

Since the ferroelectric film serving as the capacitor insulating films 625 is thus formed in the openings 623 having the tapered wall surfaces, the ferroelectric film containing the plurality of elements as the components thereof is excellently uniform in
25 thickness and composition. That is, the formation of the openings 623 into the tapered

configuration allows the sidewalls of the third interlayer insulating film 622 to be gently sloped at the bent portions of the openings 623 around the bottom surfaces thereof so that the ferroelectric film having a uniform thickness is formed successfully. As a result, the ferroelectric film serving as the capacitor insulating films 625 has a composition which is stable in any region of the openings 623, which allows easy control of the composition of the formed film.

Even if the ferroelectric film serving as the capacitor insulating films 625 is formed by sputtering instead of MOCVD, a ferroelectric film having a uniform thickness can be obtained provided that the openings 623 have a tapered configuration, since sputtered atoms are anisotropic.

Next, platinum having a film thickness of about 50 nm is deposited by sputtering on the ferroelectric film serving as the capacitor insulating films 625. Then, the platinum and the ferroelectric film are patterned to form the capacitor insulating films 625 each composed of the upper electrode 626 made of the platinum and the ferroelectric film. The upper electrodes 626 also serve as the cell plates 650. Although the capacitor insulating films 625 and the upper electrodes 626 are formed by the same patterning step, it is not limited thereto.

Since the lower electrode 624 and the upper electrode 626 are formed in each of the openings 623 having the tapered configuration, it is possible to provide the lower electrode 624 and the upper electrode 626 each having a sufficient thickness over the entire region formed with the capacitor so that a broken wire occurring during the crystallization of the ferroelectric film by high-temperature annealing is prevented reliably.

In this manner, the capacitors 627 each composed of the lower electrode 624, the capacitor insulating film 625, and the upper electrode 626 are formed in the individual openings 623. The capacitors 627 are connected electrically to the source diffusion layers

613b of the MOS transistors via the lower electrodes 624, the oxygen barrier films 621, the conductive lower hydrogen barrier films 620, and the second contact plugs 619.

Although the platinum having a film thickness of about 50 nm is used in the lower electrode 624 and the upper electrode 626, it is also possible to use, instead of the platinum, another platinum group element, i.e., ruthenium (Ru), rhodium (Rh), palladium (Pd), osmium (Os), gold, (Au), iridium (Ir), or an oxide thereof or, alternatively, titanium (Ti), titanium-aluminum (TiAl), tantalum (Ta), tantalum-aluminum (TaAl), a nitride thereof, or a multilayer film composed thereof. Preferably, the film thickness of each of the lower electrode 624 and the upper electrode 626 is on the order of 10 nm to 200 nm.

Preferably, the capacitor insulating film 625 is composed of a ferroelectric film or a high dielectric film. For the ferroelectric film, a ferroelectric material of, e.g., $\text{SrBi}_2(\text{Ta}_x\text{Nb}_{1-x})_2\text{O}_9$, $\text{Pb}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$, $(\text{Ba}_x\text{Sr}_{1-x})\text{TiO}_3$, or $(\text{Bi}_x\text{La}_{1-x})_4\text{Ti}_3\text{O}_{12}$ (where X satisfies the relationship represented by $0 \leq x \leq 1$) may be used appropriately. For the high dielectric film, a high dielectric material of, e.g., a tantalum pentaoxide (Ta_2O_5) can be used appropriately. Preferably, the thickness of the capacitor insulating film 625 is on the order of 20 nm to 200 nm.

- Formation of Insulating Upper Hydrogen Barrier Film -

Next, as shown in FIG. 14B, a silicon oxide is deposited by CVD over the entire surface of the semiconductor substrate 610 in such a manner as cover the capacitors 627, thereby forming a fourth interlayer insulating film 628. Subsequently, the portions of the fourth interlayer insulating film 628 and the third interlayer insulating film 622 formed outside the cell block are removed by lithography and dry etching by masking a region covering the cell block (not shown), whereby the end portion of the insulating lower hydrogen barrier film 618 is exposed.

Next, the insulating upper hydrogen barrier film 629 composed of a titanium-

aluminum oxide having a film thickness of about 50 nm is deposited by sputtering on the fourth interlayer insulating film 628, the third interlayer insulating film 622, and the exposed surface of the insulating lower hydrogen barrier film 618. As a result, the insulating upper hydrogen barrier film 629 is connected to the insulating lower hydrogen barrier film 618 at the connecting portion 629a at the peripheral edge portion of the cell block.

Next, a silicon oxide is deposited by CVD over the entire surface of the semiconductor substrate 610 in such a manner as to cover the insulating upper hydrogen barrier film 629, thereby forming a fifth interlayer insulating film 630.

10 - Formation of Wiring -

Next, as shown in FIG. 15, a contact hole is formed in the region of the fifth interlayer insulating film 630 formed outside the connecting portion 629a to extend through the fifth and second interlayer insulating films 630 and 617 and expose the upper surface of the bit line 616. Then, a titanium film, a titanium nitride film, and tungsten are buried successively in the contact hole to form a third contact plug 631 connected to the bit line 616. Subsequently, a titanium film having a thickness of about 10 nm, a titanium nitride film having a thickness of about 50 nm, an aluminum film having a thickness of about 500 nm, and a titanium nitride film having a thickness of about 50 nm are deposited successively by sputtering on the fifth interlayer insulating film 630, thereby forming wiring 632 connected to the third contact plug 631.

Thereafter, a desired semiconductor device is obtained by a well-known fabrication process including the formation of multilayer wiring, the formation of a protective film, and the formation of pads.

Thus, in accordance with the method for fabricating the semiconductor device according to the sixth embodiment, the insulating lower hydrogen barrier film 618 is

provided under the cell block including the plurality of capacitors 627 and the dummy capacitors 627A for conduction, while the insulating upper hydrogen barrier film 629 connected to the insulating lower hydrogen barrier film 618 at the connecting portion 629a is provided over the cell block and sidewise thereof. The arrangement prevents hydrogen generated in the step of wiring formation or the like after the formation of the insulating upper hydrogen barrier film 629 from entering the capacitors 627 and thereby suppresses the degradation of the characteristics of the capacitors 627 resulting from the reduction of the capacitor insulating films 625 by hydrogen.

Since the second contact plugs 619 extending through the insulating lower hydrogen barrier film 618 has upper sidewalls thereof in contact with the insulating lower hydrogen barrier film 618 and upper ends thereof covered with the conductive lower hydrogen barrier film 620, the entrance of hydrogen from between the insulating lower hydrogen barrier film 618 and the conductive lower hydrogen barrier film 620 can be prevented. This prevents the reduction of the capacitor insulating films 625 resulting from the entrance of hydrogen.

In addition, since the capacitors are formed in the openings having tapered wall surfaces in the semiconductor device according to the sixth embodiment, capacitors free from a broken wire can be implemented. Moreover, since the capacitors are enclosed by the hydrogen barrier films, it becomes possible to prevent the entrance of hydrogen into the capacitors and thereby suppress the degradation of the characteristics of the capacitors.